FAIRCHILD SEMICONDUCTOR®

August 2012

FDMC7208S

Dual N-Channel PowerTrench® MOSFET

Q1: 30 V, 12 A, 9.0 mΩ Q2: 30 V, 16 A, 6.4 mΩ

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 9.0 mΩ at V_{GS} = 10 V, I_D = 12 A
- Max $r_{DS(on)}$ = 11.0 mΩ at V_{GS} = 4.5 V, I_D = 11 A

Q2: N-Channel

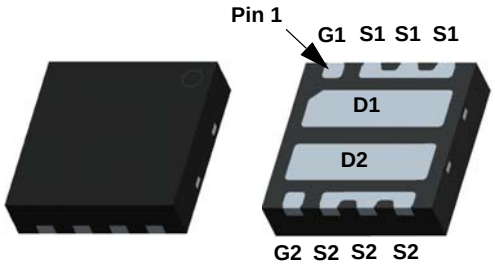
- Max $r_{DS(on)}$ = 6.4 mΩ at V_{GS} = 10 V, I_D = 16 A
- Max $r_{DS(on)}$ = 7.5 mΩ at V_{GS} = 4.5 V, I_D = 13.5 A
- Termination is Lead-free and RoHS Compliant

General Description

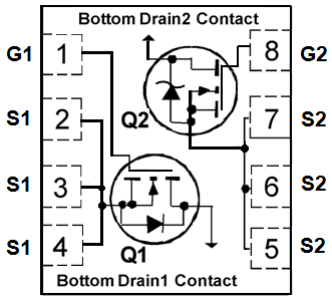
This device includes two 30V N-Channel MOSFETs in a dual Power 33 (3 mm X 3 mm MLP) package. The package is enhanced for exceptional thermal performance.

Applications

- Computing
- Communications
- General Purpose Point of Load
- Notebook System



Power 33



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter		Q1	Q2	Units
V_{DS}	Drain to Source Voltage		30	30	V
V_{GS}	Gate to Source Voltage	(Note 4)	±20	±12	V
I_D	Drain Current -Continuous (Package limited)	T_C = 25 °C	22	26	A
	-Continuous	T_A = 25 °C	12[1a]	16[1b]	
	-Pulsed		60	80	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	21	21	mJ
P_D	Power Dissipation for Single Operation	T_A = 25 °C	1.9[1a]	1.9[1b]	W
	Power Dissipation for Single Operation	T_A = 25 °C	0.8[1c]	0.8[1d]	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	65[1a]	65[1b]	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	155[1c]	155[1d]	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC7208S	FDMC7208S	Power 33	13 ”	12 mm	3000 units

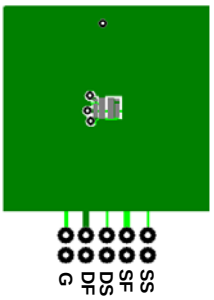
Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V I_D = 1 mA, V_{GS} = 0 V	Q1 Q2	30 30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C I_D = 10 mA, referenced to 25 °C	Q1 Q2		27 21		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V	Q1 Q2			1 500	μA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = 20 V, V_{DS}= 0 V V_{GS} = 12 V, V_{DS}= 0 V	Q1 Q2			100 100	nA
On Characteristics							
$V_{GS(th)}$	Gate to Source Threshold Voltage	I_D = 250 μA, V_{GS} = 0 V I_D = 1 mA, V_{GS} = 0 V	Q1 Q2	1.2 1.2	1.7 1.6	3.0 3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C I_D = 10 mA, referenced to 25 °C	Q1 Q2		-5 -3		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10 V, I_D = 12 A V_{GS} = 4.5 V, I_D = 11 A V_{GS} = 10 V, I_D = 12 A, T_J = 125 °C	Q1		6.7 8.8 9.2	9.0 11.0 12.4	mΩ
		V_{GS} = 10 V, I_D = 16 A V_{GS} = 4.5 V, I_D = 13.5 A V_{GS} = 10 V, I_D = 16 A , T_J = 125 °C	Q2		4.7 5.3 6.4	6.4 7.5 6.8	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 12 A V_{DS} = 5 V, I_D = 16 A	Q1 Q2		53 80		S
Dynamic Characteristics							
C_{iss}	Input Capacitance	Q1: V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHZ	Q1 Q2		848 1685	1130 2245	pF
C_{oss}	Output Capacitance	Q2: V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHZ	Q1 Q2		270 432	360 575	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		36 42	55 65	pF
R_g	Gate Resistance		Q1 Q2	0.1 0.1	1.1 1.0	2.5 2.5	Ω
Switching Characteristics							
$t_{d(on)}$	Turn-On Delay Time	Q1: V_{DD} = 15 V, I_D = 12 A, R_{GEN} = 6 Ω Q2: V_{DD} = 15 V, I_D = 16 A, R_{GEN} = 6 Ω	Q1 Q2		6 7	12 14	ns
t_r	Rise Time		Q1 Q2		2 3	10 10	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		16 23	29 36	ns
t_f	Fall Time		Q1 Q2		2 2	10 10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V Q1 V_{DD} = 15 V, I_D = 12 A	Q1 Q2		13 26	18 36	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 5 V Q1 V_{DD} = 15 V, I_D = 12 A	Q1 Q2		6.7 14	9.4 20	nC
Q_{gs}	Gate to Source Gate Charge	Q2 V_{DD} = 15 V, I_D = 16 A	Q1 Q2		2.3 3.9		nC
Q_{gd}	Gate to Drain “Miller” Charge	Q2 V_{DD} = 15 V, I_D = 16 A	Q1 Q2		1.8 2.7		nC

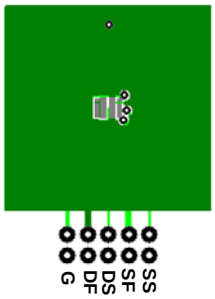
Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Drain-Source Diode Characteristics							
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2 A (Note 2) V_{GS} = 0 V, I_S = 12 A (Note 2) V_{GS} = 0 V, I_S = 2 A (Note 2) V_{GS} = 0 V, I_S = 16 A (Note 2)	Q1 Q1 Q2 Q2		0.72 0.82 0.70 0.82	1.2 1.2 1.2 1.2	V
t_{rr}	Reverse Recovery Time	Q1 I_F = 12 A, di/dt = 100 A/µs	Q1 Q2		21 21	34 33	ns
Q_{rr}	Reverse Recovery Charge	Q2 I_F = 16 A, di/dt = 300 A/µs	Q1 Q2		6 16	12 28	nC

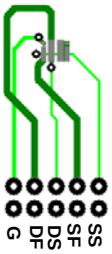
Notes:
1.$R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 65 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 65 °C/W when mounted on a 1 in^2 pad of 2 oz copper



c. 155 °C/W when mounted on a minimum pad of 2 oz copper

d. 155 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 µs, Duty cycle < 2.0%.
3. Q1: E_{AS} of 21 mJ is based on starting T_J = 25 °C, L = 0.3 mH, I_{AS} = 12 A, V_{DD} = 27 V, V_{GS} = 10 V. 100% tested at L = 3 mH, I_{AS} = 5.2 A.
Q1: E_{AS} of 21 mJ is based on starting T_J = 25 °C, L = 0.3 mH, I_{AS} = 12 A, V_{DD} = 27 V, V_{GS} = 10 V. 100% tested at L = 3 mH, I_{AS} = 5.4 A.
4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

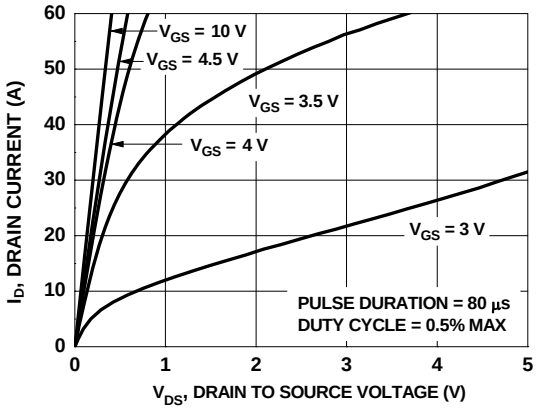


Figure 1. On Region Characteristics

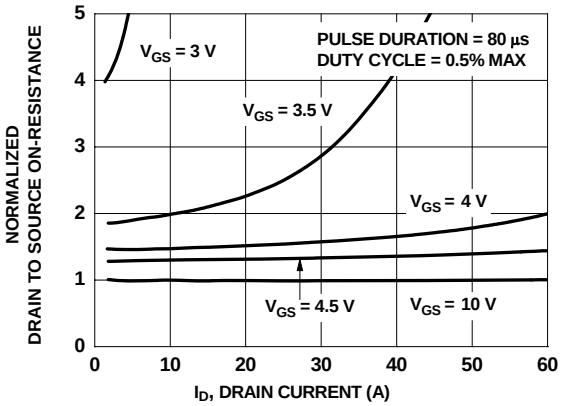


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

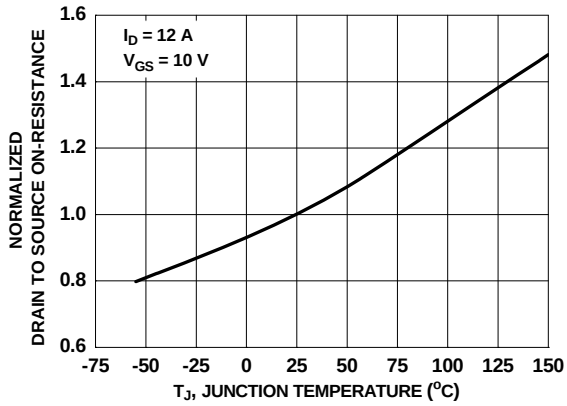


Figure 3. Normalized On Resistance vs Junction Temperature

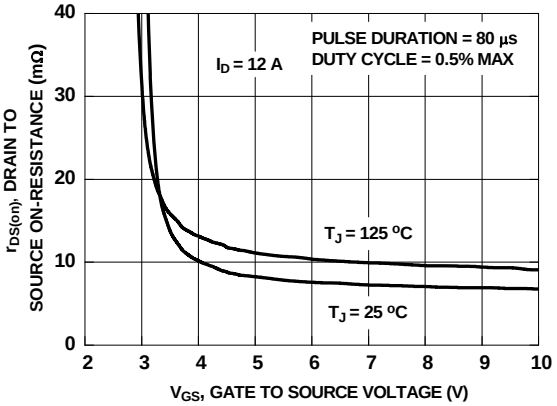


Figure 4. On-Resistance vs Gate to Source Voltage

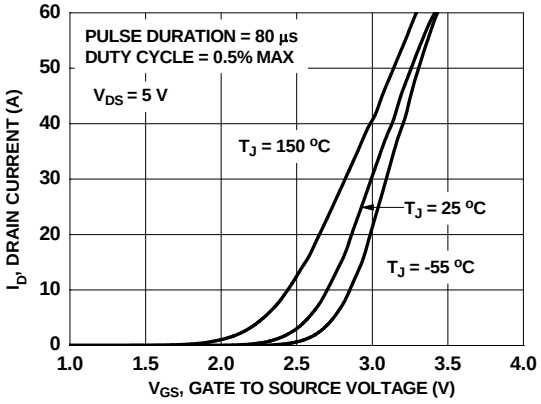


Figure 5. Transfer Characteristics

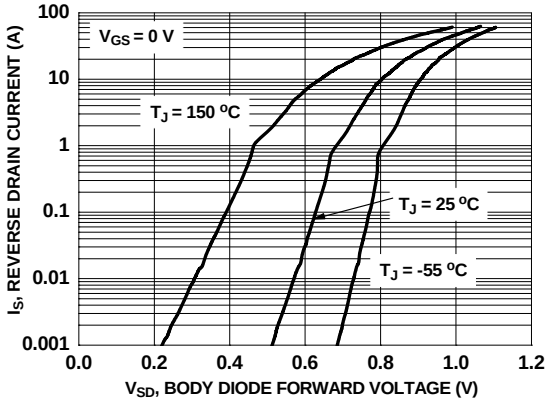


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

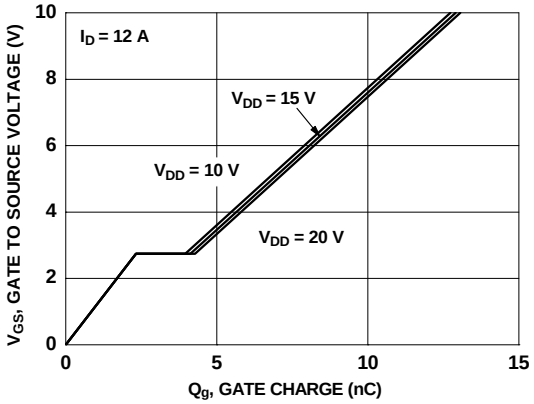


Figure 7. Gate Charge Characteristics

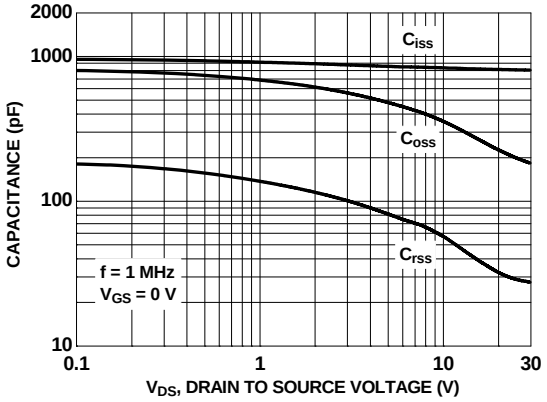


Figure 8. Capacitance vs Drain to Source Voltage

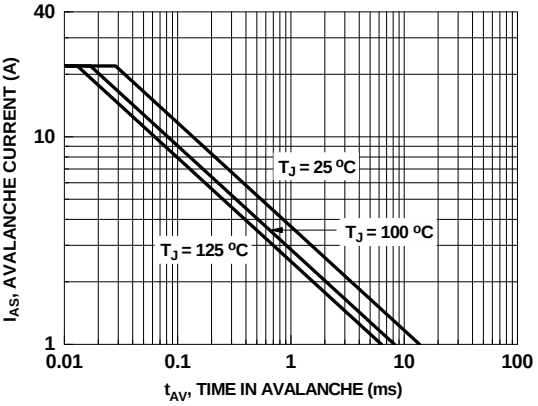


Figure 9. Unclamped Inductive Switching Capability

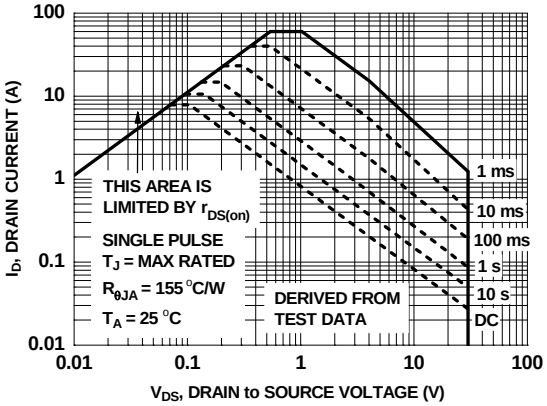


Figure 10. Forward Bias Safe Operating Area

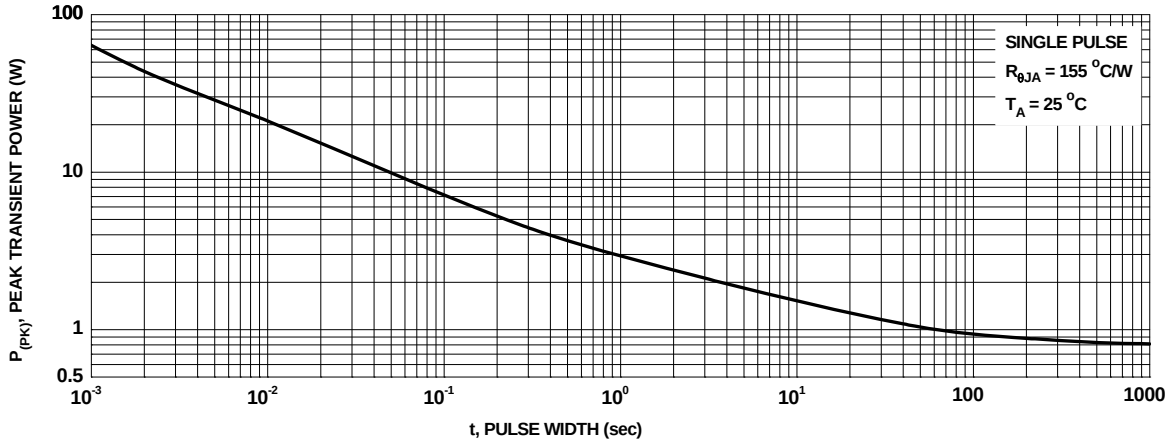


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

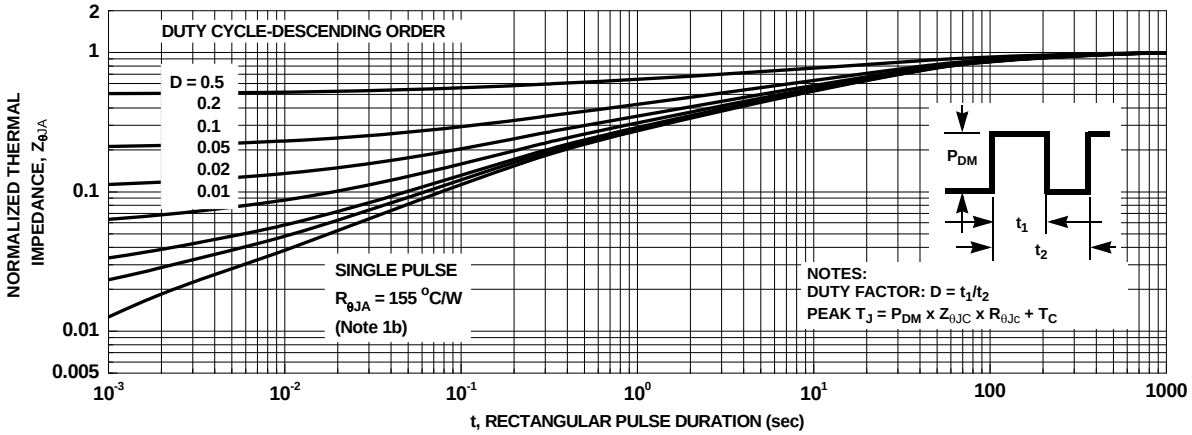


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (Q2 N-Channel) T_J = 25 °C unless otherwise noted

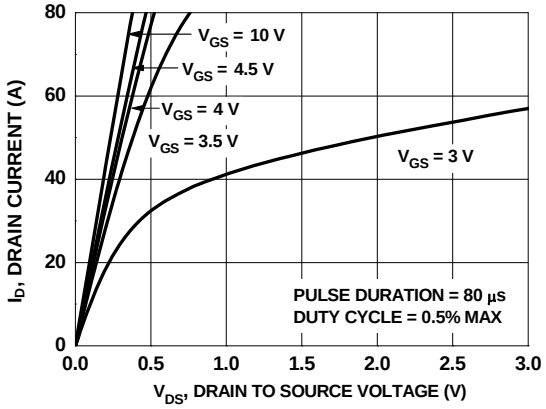


Figure 14. On- Region Characteristics

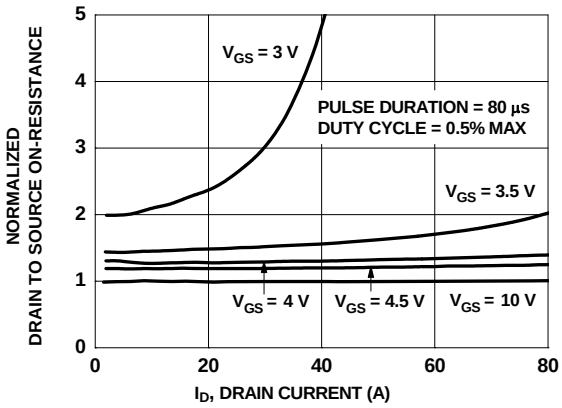


Figure 15. Normalized on-Resistance vs Drain Current and Gate Voltage

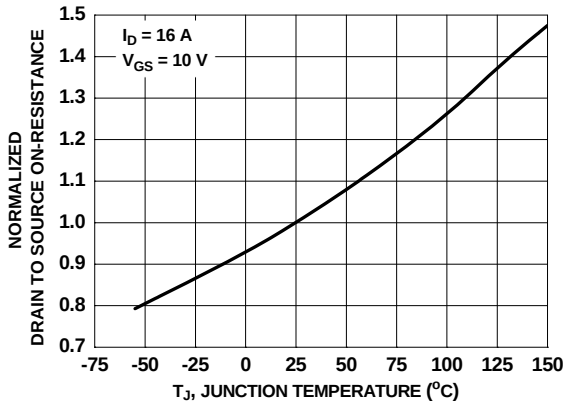


Figure 16. Normalized On-Resistance vs Junction Temperature

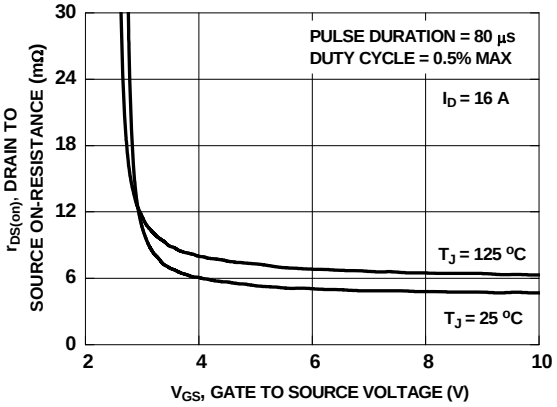


Figure 17. On-Resistance vs Gate to Source Voltage

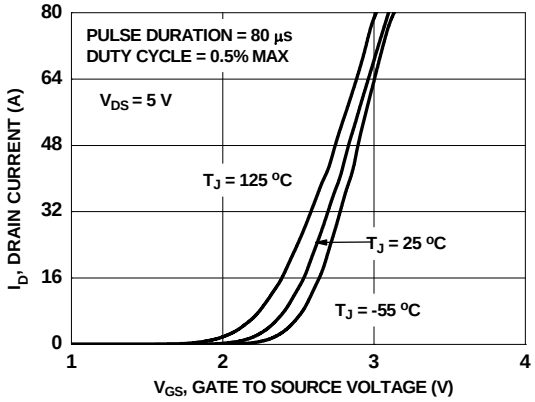


Figure 18. Transfer Characteristics

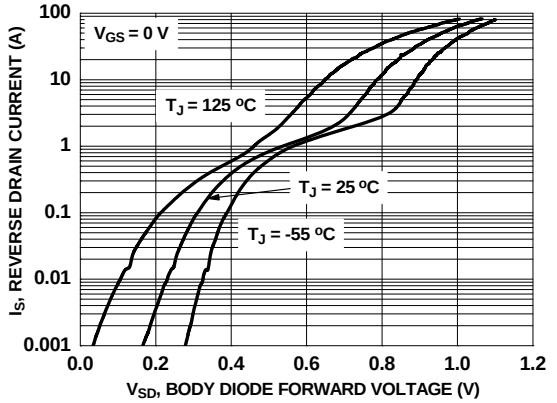


Figure 19. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q2 N-Channel) T_J = 25°C unless otherwise noted

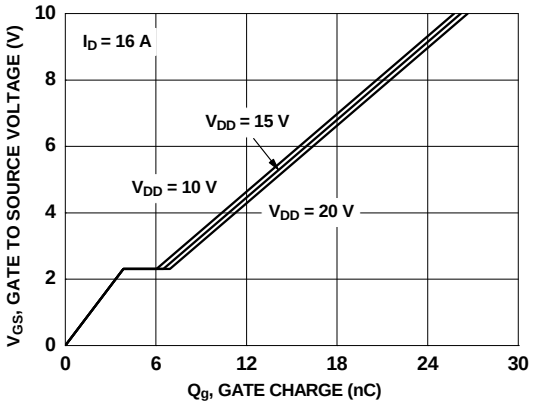


Figure 20. Gate Charge Characteristics

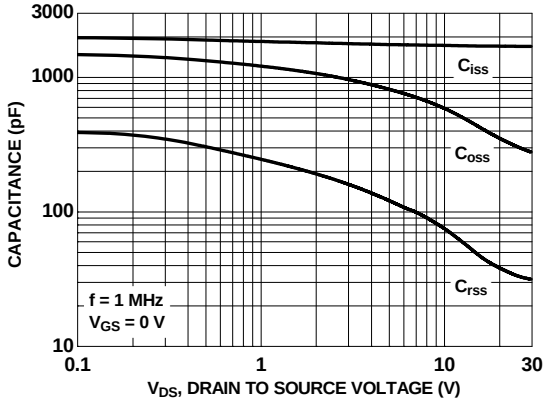


Figure 21. Capacitance vs Drain to Source Voltage

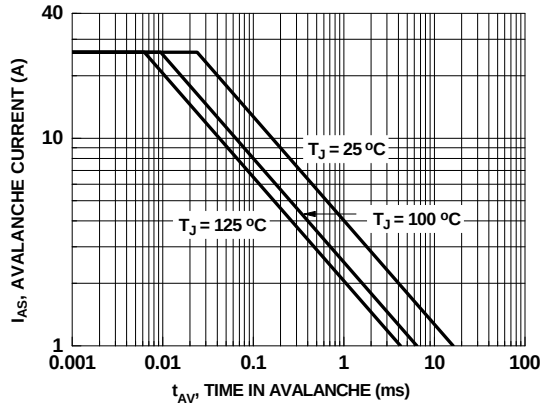


Figure 22. Unclamped Inductive Switching Capability

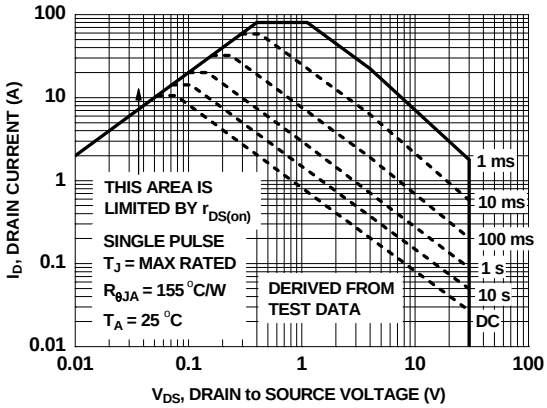


Figure 23. Forward Bias Safe Operating Area

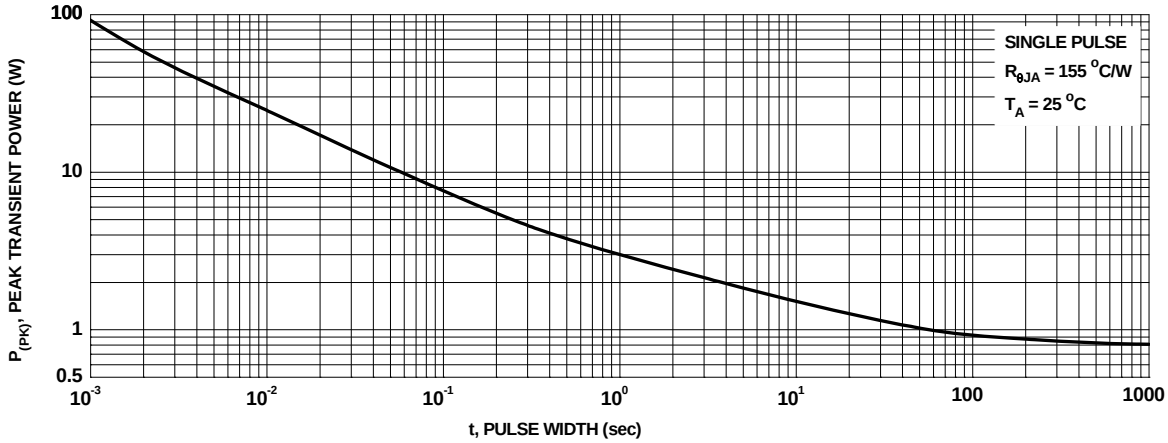


Figure 24. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q2 N-Channel) T_J = 25 °C unless otherwise noted

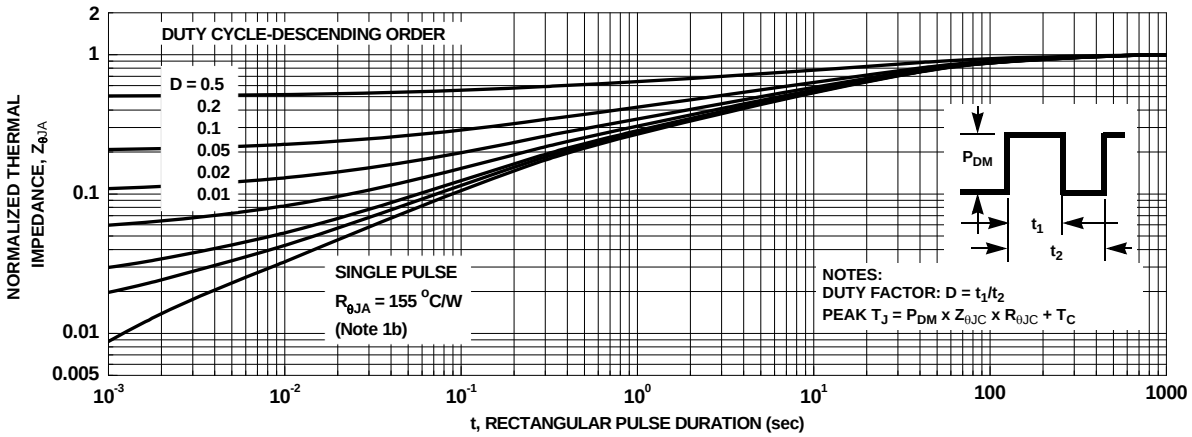


Figure 26. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET™ Schottky body diode Characteristics

Fairchild's SyncFET™ process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 27 shows the reverses recovery characteristic of the FDMC7208S.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

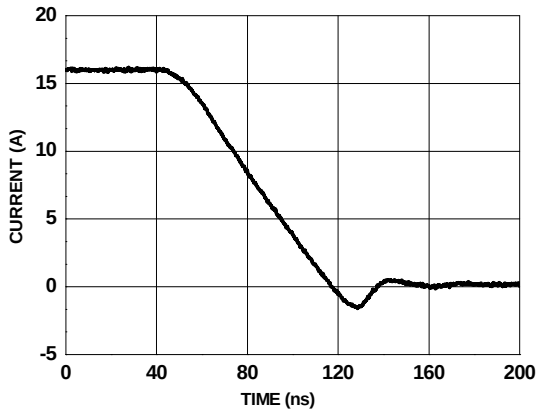


Figure 27. FDMC7208S SyncFET™ body diode reverse recovery characteristic

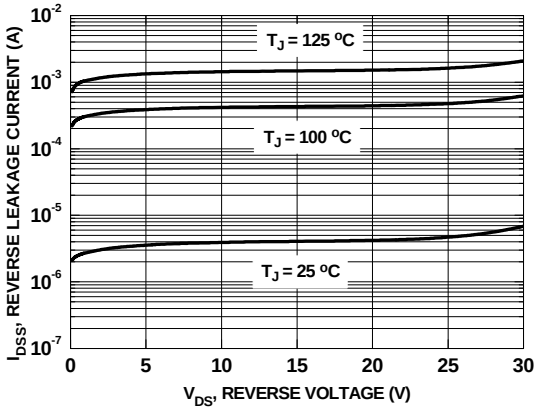
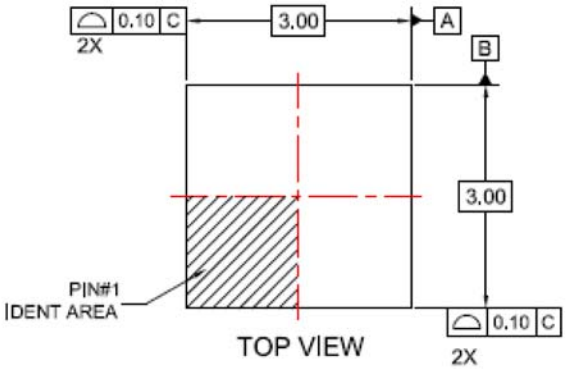
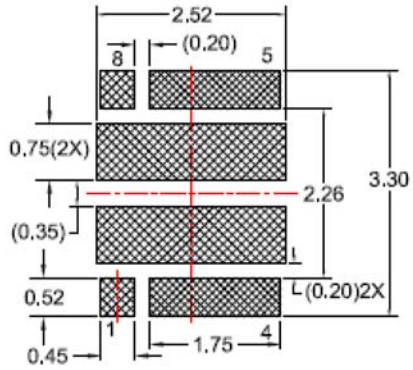


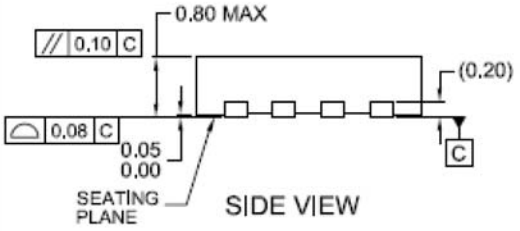
Figure 28. SyncFET™ body diode reverses leakage versus drain-source voltage

Dimensional Outline and Pad Layout





RECOMMENDED LAND PATTERN



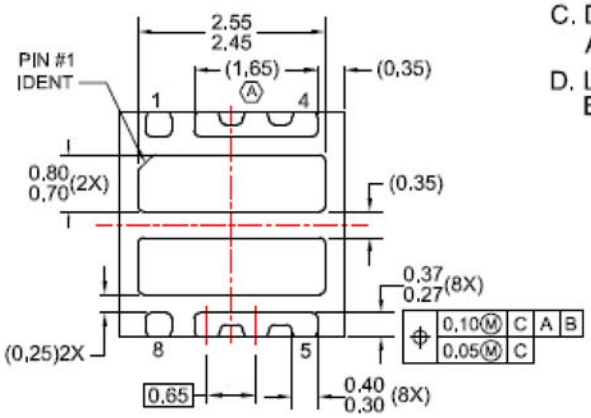
NOTES:

A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229,

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994

D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY



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AccuPower™
AX-CAP™*
BitSiC®
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficentMax™
ESBC™
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FlashWriter® *
FPS™
F-PFS™
FRFET®
Global Power Resource^{SM}
Green Bridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Marking Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
Motion-SPM™
mWSaver™
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW/W/kW at a time™
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Rev. I61